

Supporting Information***In situ Disorder-Order Transformation in
Synthetic Gallosilicate Zeolites with the NAT Topology***

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Table 1S. Fractional Atomic Coordinates of the Asymmetric Units of the Four Optimized Periodic Models Considered for *Ab Initio* Calculations (ω_1 , τ_1 , τ_2 , τ_3 ; See Table 1 and Text). In All Cases, the Primitive Cell Choice, with Parameters: $a = b = c = 9.90788 \text{ \AA}$, $\alpha = \beta = 96.4919^\circ$, and $\gamma = 140.7032^\circ$, Has Been Considered.

Model ω_1

atom	x	y	z
Si	-0.0607	0.0112	0.1981
Ga	-0.1842	-0.4955	-0.4342
Si	-0.4885	-0.4885	0.0000
O	0.1663	0.1027	0.2022
O	-0.4380	0.2621	0.4077
O	0.3626	-0.0152	0.1307
O	-0.2819	-0.2644	0.1442
O	0.0672	-0.2860	-0.4830
Na	0.3605	0.2879	0.4404

Model τ_1

atom	x	y	z
Si	-0.0627	0.0101	0.1892
Ga	-0.2046	0.4973	-0.4386
Si	-0.5000	-0.5000	0.0000
Si	0.2500	-0.2500	-0.5000
O	0.1032	0.0088	0.1764
O	-0.4666	0.2450	0.4209
O	0.3536	-0.0035	0.1121
O	-0.3267	-0.2548	0.1216
O	0.0453	-0.3012	0.4975
Na	0.1799	0.0008	0.4235

Model τ_2

atom	x	y	z
Ga	-0.0812	0.0099	0.1766
Si	-0.1655	-0.2605	-0.1737
Si	-0.2434	0.1690	-0.3261
Si	0.4995	0.0829	0.3107
Si	0.4931	0.4874	-0.0026
O	0.0983	0.0063	0.1760
O	-0.1644	-0.0932	-0.1561
O	-0.2673	0.3151	-0.3011
O	-0.3412	0.0733	0.2991
O	0.3750	0.0216	0.1466
O	-0.1250	0.2010	-0.1740
O	-0.2233	-0.3668	-0.3380
O	-0.3816	-0.2852	0.1104
O	-0.3622	-0.4636	-0.1080
O	-0.4960	-0.0997	-0.4035
O	0.3044	-0.1225	0.3735
Na	0.3460	-0.3923	0.2194

Model τ_3

atom	<i>x</i>	<i>y</i>	<i>z</i>
Si	-0.0880	0.0004	0.1779
Si	-0.1554	-0.4782	-0.4148
Si	-0.2209	0.2023	-0.3188
Si	0.2356	0.0534	0.0781
Ga	0.4852	0.4852	0.0000
Ga	0.2715	-0.2285	-0.5000
O	0.1411	0.0952	0.1778
O	-0.3901	0.2880	0.4549
O	-0.1026	0.4473	-0.2997
O	0.0124	-0.1896	-0.0503
O	0.3772	0.0503	0.1742
O	-0.2034	-0.3718	-0.3329
O	-0.3088	-0.2654	0.1581
O	0.0564	-0.2850	-0.4678
O	-0.4873	0.0176	-0.3422
O	0.4012	0.2433	0.0007
Na	0.4213	0.1567	-0.2275

Table 2S. Experimental ^{29}Si NMR Chemical Shifts of a Completely Ordered Aluminosilicate Natrolite in the Orthorhombic Symmetry vs the Isotopic Chemical Shifts Predicted from the Average T-O-T Angles Taken in the Crystallographic Data for Two Materials with the Same Space group ($Fdd2$) and Si/Al ratio (Si/Al = 1.50)

Si site	multiplicity	average $\angle\text{T-O-T}^{\text{a}}$	structural unit	^{29}Si δ (ppm)			average $\angle\text{T-O-T}^{\text{h}}$	structural unit	^{29}Si δ (ppm)		
				$\delta_{\text{prel}}^{\text{b,c}}$	$\delta_{\text{pre2}}^{\text{c,d}}$	$\delta_{\text{obs}}^{\text{e}}$			$\delta_{\text{prel}}^{\text{b,c}}$	$\delta_{\text{pre2}}^{\text{c,d}}$	$\delta_{\text{obs}}^{\text{e}}$
Si ₂	8	142.5	Si ₂ (4Al)	-85.4	-86.3		142.4	Si ₂ (4Al)	-85.3	-86.2	
			Si ₂ (3Al)	-91.0	-91.3			Si ₂ (3Al)	-90.9	-91.2	
			Si ₂ (2Al)	-96.6	-96.3	-95.2		Si ₂ (2Al)	-96.5	-96.2	-95.2
			Si ₂ (1Al)	-102.2	-101.3			Si ₂ (1Al)	-102.1	-101.2	1.3
			Si ₂ (0Al)	-107.8	-106.3			Si ₂ (0Al)	-107.7	-106.2	
			Si ₁ (4Al)	-81.1	-81.6			Si ₁ (4Al)	-81.3	-81.8	
Si ₁	16	136.8	Si ₁ (3Al)	-86.7	-86.6	-87.6	137.0	Si ₁ (3Al)	-86.9	-86.8	
			Si ₁ (2Al)	-92.3	-91.6			Si ₁ (2Al)	-92.5	-91.8	
			Si ₁ (1Al)	-97.9	-96.6			Si ₁ (1Al)	-98.1	-96.8	
			Si ₁ (0Al)	-103.5	-101.6			Si ₁ (0Al)	-103.7	-101.8	

^aAverage T-O-T angles in degrees from the crystallographic data reported by Artioli et al. (*Acta Cryst.* **1984**, *C40*, 1658). ^bPredicted chemical shifts from the average T-O-T angles using the equation of Ramdas and Klinowskii (*Nature* **1984**, *308*, 521). ^cThe T₁ sites with a multiplicity of 16 are assumed to be exclusively occupied by Al atoms. ^dPredicted chemical shifts from the average T-O-T angles using the equation of Radeglia and Engelhardt (*Chem. Phys. Lett.* **1985**, *114*, 28). ^eExperimental chemical shifts reported by Neuhoff et al. (*Am. Mineral.* **2002**, *87*, 1307). ^f $\Delta\delta_1 = \delta_{\text{obs}} - \delta_{\text{prel}}$. ^g $\Delta\delta_2 = \delta_{\text{obs}} - \delta_{\text{pre2}}$. ^hAverage T-O-T angles in degrees from the crystallographic data reported by Meneghinello et al. (*Microporous Mesoporous Mater.* **1999**, *30*, 89).

Table 3S. Chemical Shifts and Relative Intensities of the ^{29}Si MAS NMR Resonances from the Six Gallosilicate NAT Materials Prepared at 150 °C for 3-23 days and Their Si/Ga Ratios Calculated by ^{29}Si MAS NMR

line ID ^a	NAT-150-3			NAT-150-5			NAT-150-7			NAT-150-10			NAT-150-14			NAT-150-23		
	δ , ppm	$I, \%$																
A	-74.3	1.6	-74.5	1.6	-74.3	1.5	-74.3	0.7	-74.3	0.7	-74.3	0.7	-74.3	0.7	-74.3	1.1		
B	-79.1	10.7	-78.9	8.7	-78.0	9.5	-78.7	5.7	-78.6	2.8	-78.6	2.8	-78.6	1.9	-78.6	1.9		
C	-82.0	4.4	-81.9	3.7	-81.7	7.8	-82.0	5.0	-82.0	4.2	-82.0	4.2	-82.0	5.2	-82.0	5.2		
D	-84.7	30.0	-84.6	37.0	-83.7	35.4	-84.3	42.6	-84.3	55.5	-84.3	55.5	-84.3	53.5	-84.3	53.5		
E	-88.3	15.3	-88.1	11.7	-87.4	12.1	-87.6	11.3	-87.0	5.8	-87.0	5.8	-87.0	6.7	-87.0	6.7		
F	-91.0	11.0	-91.0	7.4	-91.0	7.4	-91.0	7.2	-91.0	4.2	-91.0	4.2	-91.0	4.8	-91.0	4.8		
G	-94.2	14.9	-94.4	17.0	-93.7	16.8	-94.1	20.1	-94.1	23.0	-94.1	23.0	-94.1	23.6	-94.1	23.6		
H	-98.4	8.5	-98.4	7.6	-98.0	7.5	-98.0	5.6	-97.5	2.8	-97.5	2.8	-97.5	1.9	-97.5	1.9		
I	-101.5	3.6	-101.5	5.3	-101.5	2.0	-101.3	1.8	-101.3	1.0	-101.3	1.0	-101.3	1.3	-101.3	1.3		
$\text{Si}/\text{Ga}_{\text{nmr}, f, 42d}^{\text{b}}$	1.75	1.78	1.78	1.69	-	-	-	-	-	-	-	-	-	-	-	-		
$\text{Si}/\text{Ga}_{\text{nmr}, f, d2}^{\text{c}}$	1.51 (1.55)	1.53 (1.58)	1.46 (1.59)	1.49 (1.55)	1.47 (1.57)	1.47 (1.57)	1.47 (1.57)	1.47 (1.57)	1.47 (1.57)	1.47 (1.57)	1.47 (1.57)	1.47 (1.57)	1.47 (1.57)	1.47 (1.57)	1.47 (1.57)	1.47 (1.57)		
$I_{\text{D}}/I_{\text{G}}^{\text{d}}$	2.01	2.18	2.19	2.12	2.12	2.41	2.41	2.41	2.41	2.27	2.27	2.27	2.27	2.27	2.27	2.27	2.27	
$\text{Si}/\text{Ga}_{\text{nmr}, \text{D-G}}^{\text{e}}$	1.50	1.49	1.49	1.49	1.49	1.49	1.49	1.49	1.49	1.48	1.48	1.48	1.48	1.48	1.48	1.48	1.48	

^aLine ID's are the same as those given in Figure 7 or Table 3. ^bThe Si/Ga ratio calculated from the tetragonal assignments of their ^{29}Si MAS NMR NMR data. The values for NAT-150-10, NAT-150-14, and NAT-150-23 were not calculated here, since the XRD patterns of these three materials were not indexable as tetragonal. ^cThe Si/Ga ratio calculated according to the orthorhombic assignments of their NMR data. The values in parentheses are the Si/Ga ratio determined by elemental analysis. ^dThe relative intensity ratio of Line D to Line G that are assigned to $\text{Si}_1(3\text{Ga})$ and $\text{Si}_2(2\text{Ga})$ species in the orthorhombic model, respectively. ^eThe Si/Ga ratio calculated using lines D and G only based on the orthorhombic assumption.

Table 4S. Fractional Occupation of Ga in the Different Nonequivalent T-sites for the Ordered and Disordered Simulated Structures

Si/Ga	<i>ordered</i>		<i>disordered</i>		
	1.50	1.50	1.53	1.55	1.58
T ₁	0.00	0.44	0.43	0.43	0.43
T' ₁	1.00	0.44	0.44	0.43	0.43
T ₂	0.00	0.25	0.24	0.23	0.21

Table 5S. Percentages of 4-Rings Composed only of T₁ Sites with *n*Ga Atoms for the Ordered and Disordered Simulated Structures^a

<i>n</i> // Si/Ga	<i>ordered</i>		<i>disordered</i>		
	1.50	1.50	1.53	1.55	1.58
0	0.0	1.94	1.95	1.94	1.92
1	0.0	21.53	22.46	23.13	23.90
2	100.0	76.29	75.34	74.67	73.90

^a The very low percentage (< 0.3%) for the presence of 3 Ga atoms per 4-ring in each disordered structure, yielding violations of Loewenstein's rule, is not included.

Figure 1S. (a) ^{71}Ga and (b) ^{23}Na MAS NMR spectra of the NAT-150-3 (bottom) and NAT-150-23 (top) materials recorded at 150 °C. Spinning side bands are marked by asterisks.

Figure 2S. ^{29}Si MAS NMR spectra of (a) NAT-150-3, (b) NAT-150-5, (c) NAT-150-7, (d) NAT-150-10, (e) NAT-150-14, and (f) NAT-150-23 materials: experimental (top); simulated (middle); deconvoluted components (bottom). The best-simulated spectrum was obtained when the experimental one for each gallosilicate material is deconvoluted into 9 components denoted (from left to right) as lines A-I.

Figure 3S. Si($n\text{Ga}$) populations as a function of the orthorhombic distortion. The populations calculated for the “disordered” model derived by *Monte Carlo* sampling ($\text{Si/Ga} = 1.58$) are shown at $\delta_o = 0.000$, while those corresponding to the ordered model are arbitrarily depicted at $\delta_o = 0.029$. The rest of values correspond to the experimental ones obtained from the orthorhombic assignment of the ^{29}Si MAS NMR data. The square, diamond, and circle denote T_1 , T_2 , and total T ($T_1 + T_2$) populations, respectively.

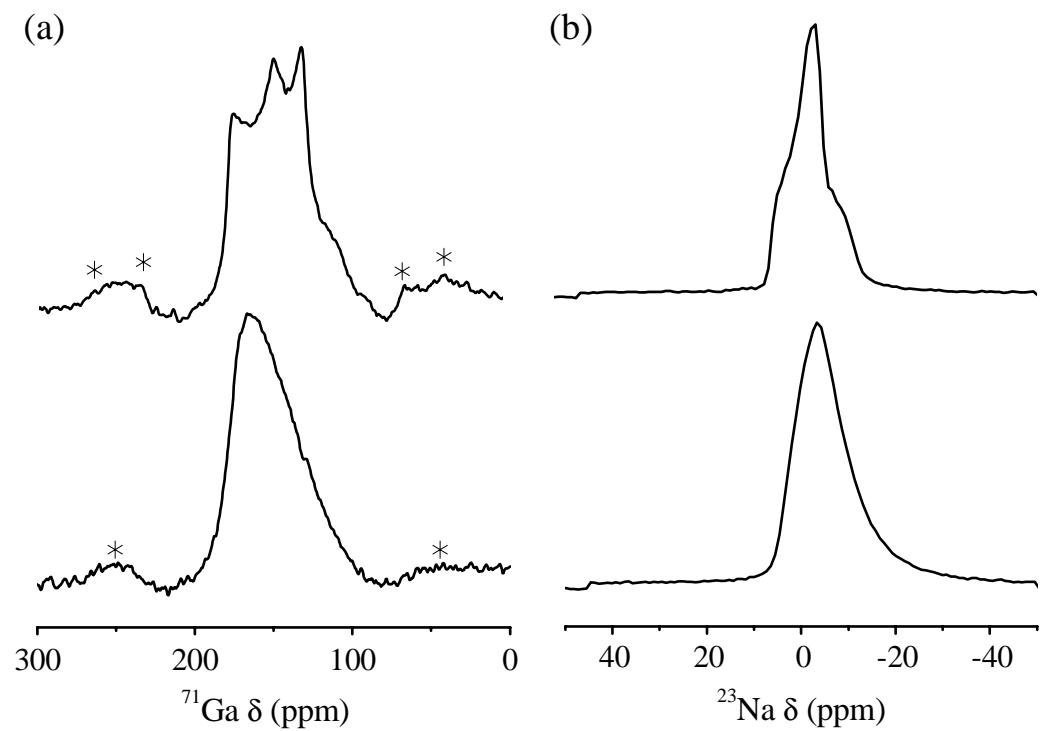


Figure 1S

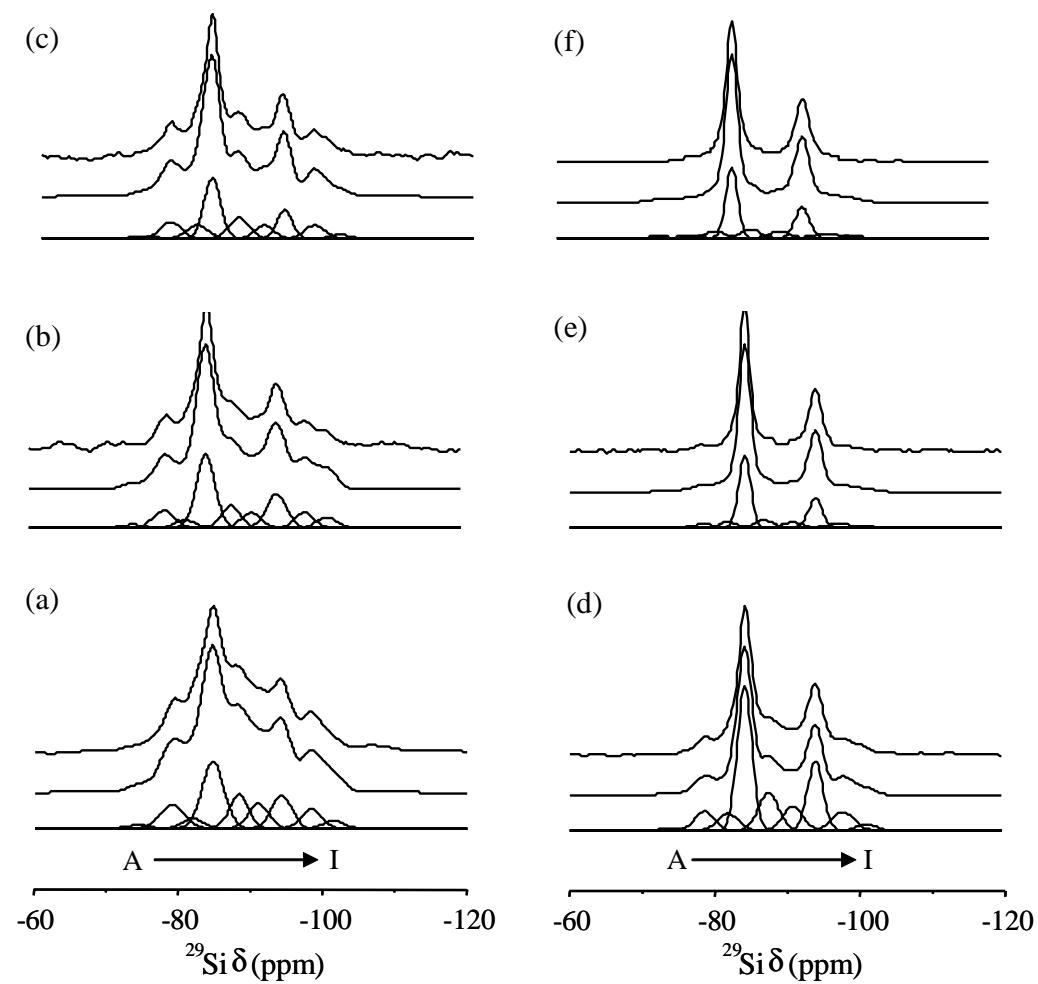


Figure 2S

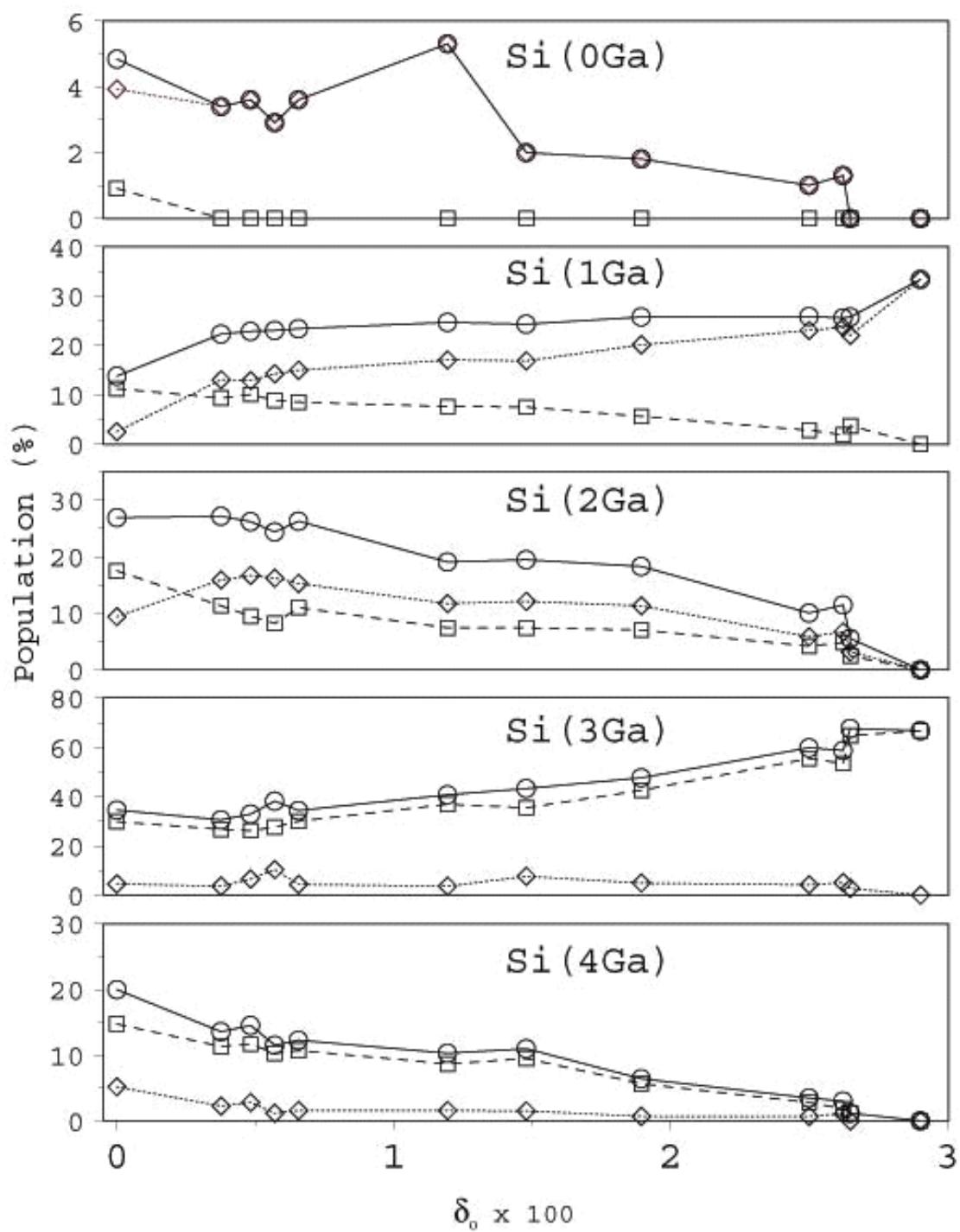


Figure 3S